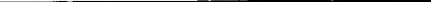


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/715,971
				Filing Date	November 17, 2003
				First Named Inventor	Shahriar Ahmed
				Art Unit	2812
				Examiner Name	
				Attorney Docket Number	42P17289
Sheet	1	of	2		

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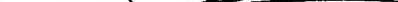
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				Application Number	10/715,971
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				Art Unit	2812
				Examiner Name	
				Attorney Docket Number	42P17289
Sheet	2	of	2		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>TSP</i>		Ida, Minoru et al., "Enhancement of fmax in InP/InGaAs HBTs by Selective MOCVD Growth of Heavily-Doped Extrinsic Base Regions," IEEE Trans on Elect Devices, Vol. 43, No. 11, Nov 1996, pgs. 1812-1817.

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